

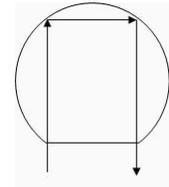
Part Number	Customer
-------------	----------

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	Wafer Vendor
	2.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	4.0	Overall Thickness	503.00 +/- 16.00 μ m	ADE, 100%
	5.0	Total Thickness Variation (TTV)	<5.00 μ m	Guaranteed by Process
	6.0	Bow	<80.00 μ m	ADE 100%, SEMI MF1530
	7.0	Warp	<80.00 μ m	ADE 100%, SEMI MF1530
	8.0	Edge Chips	none	Bright Light, 100%
	9.0	Edge Exclusion	5mm	
HandleSilicon	10.0	Handle Growth Method	CZ	Wafer Vendor
	11.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	12.0	Handle Thickness	500.00 +/- 15.00 μ m	ADE, 100%
	13.0	Handle Doping Type	P	Wafer Vendor
	14.0	Handle Dopant	Boron	Wafer Vendor
	15.0	Handle Resistivity	1 ~ 20 Ohm-cm	Wafer Vendor
	16.0	Backside Finish	Polished with oxide and laser mark	Guaranteed by process
BuriedOxide	17.0	Oxide Type	Thermal	
	18.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	19.0	Oxide formed on	Handle and/or Device Wafer	
DeviceSilicon	20.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	21.0	Nominal Thickness	2.00 +/- 0.50 μ m	100% 9-Pt (note3)
	22.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	23.0	Edge Removal Depth in Handle	<100 μ m	Guaranteed by process
	24.0	Device Doping Type	P	Wafer Vendor
	25.0	Device Dopant	Boron	Wafer Vendor
	26.0	Device Growth Method	CZ	Wafer Vendor
	27.0	Device Resistivity	<0.0025 Ohm-cm	Wafer Vendor
	28.0	Voids	None	Bright Light, 100% (note 2)
	29.0	Scratches	Frontside - no scratches allowed. Backside - light handling marks	Bright Light, 100% (note 2)
	30.0	Haze	None	Bright Light, 100% (note 2)

Part Number	Customer
-------------	----------

Category	Parameter	Specification	Measurement Method
----------	-----------	---------------	--------------------

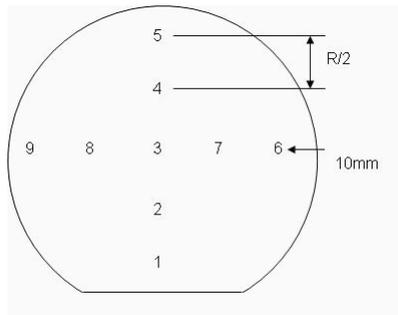
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information